



Wavelength-dependent near-infrared microbolometer for short-wavelength infrared light with gold nanowire grating optical absorber

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3 **Title** Wavelength-dependent near-infrared microbolometer for short-wavelength infrared light with gold nanowire
4 grating optical absorber

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10

11 **Abstract**

12 Near-infrared (NIR) imaging has been used for nondestructive and non-contact inspections in various areas, such as food
13 and medicine inspections and medical diagnoses. The short-wavelength infrared light (SWIR) sensor currently used
14 requires a Peltier cooler and a diffraction grating spectroscope owing to its detection principle. Thus, realizing a low-
15 cost and miniaturized SWIR imaging device remains challenging and has limitations for practical applications. In this
16 study, we propose a bolometer-type detector element fabricated using a silicon-on-insulator (SOI) wafer as a low cost
17 and miniaturized SWIR image sensor element. We adopted gold (Au) nanowire grating structures coated with silicon as
18 wavelength-dependent SWIR absorbers and aimed at wavelength-selectivity imaging without using a spectroscope. A
19 device was designed and fabricated with Au nanowire grating structures on a doubly clamped Si beam using
20 microelectromechanical system (MEMS) technology. The electrical characteristics of the device were measured
21 depending on device temperature and SWIR irradiation intensity. It was found that electrical resistance decreased linearly
22 with increasing device temperature and SWIR irradiation intensity (wavelength at 1530 nm), as semiconductors have
23 negative temperature coefficients of resistance. The results show similar trends from both finite element method (FEM)
24 analysis and theoretical calculation. The resistances at wavelengths ranging from 1530 to 1565 nm at 5 nm increment
25 were evaluated. It was confirmed that absorber-integrated bolometer device enabled wavelength-dependent response of
26 the resistance according to the absorption spectrum.

27

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32 **Conflicts of interest** The authors declare that they have no conflict of interest.

33 **Availability of data and material (data transparency)** The datasets generated during and/or analyzed
34 during the current study are available from the corresponding author on reasonable request.

35 **Code availability (software application or custom code)** Not applicable

36

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41 19H02571.

42

1 Text

2 1. Introduction

3 A near-infrared (NIR) detector that enables nondestructive and non-contact inspection has been recently used in various
4 applications, such as in food (ElMasry et al. 2012; Jiang et al. 2016; Lee et al. 2014; Wu and Sun 2013) and medicine
5 inspections (Andre 2003) and for medical diagnoses (Koizumi et al. 1999; Luo et al. 2011). The detectors currently
6 marketed for short-wavelength infrared light (SWIR, wavelength range: 1–3 μm) are known as photodiodes, which are
7 fabricated from InGaAs (Yuan et al. 2007) or InAs (Marshall et al. 2008) using a photoelectric effect. They have excellent
8 responsiveness and detection sensitivity; however, they require a Peltier cooler to reduce the dark current of the
9 photoelectric effect. Furthermore, they also require a diffraction grating spectroscopy for hyperspectral imaging, making
10 their cost reduction and miniaturization challenging. Thus, they can be limited for practical applications (Manley 2014;
11 Nicolai et al. 2007).

12 For the detection of mid-wave infrared light (MWIR, wavelength range: 3–5 μm) and long-wave infrared light (LWIR,
13 wavelength range: 8–14 μm), various studies on photon and thermal detectors have been conducted. Thermal detectors
14 utilize the temperature change of the detection elements due to infrared absorption. Recently, thermal detectors have
15 opened new opportunities for military and commercial applications owing to their small size, light weight, low power
16 consumption, and wideband wavelength detection capability, compared to photon detectors (Bhan et al. 2009; Kimata
17 2018; Tezcan et al. 2001).

18 In particular, the recent advances in microelectromechanical system (MEMS) technology allow fabrication of sensitive
19 thermal microbolometer, which is common in thermal detection technologies currently available. Bolometers measure
20 changes in infrared radiation intensity and convert it into an electrical resistance change. Bolometers absorb infrared
21 radiation, thus resulting in an electrical resistance change due to an increase in temperature. They are normally integrated
22 with CMOS (Complementary metal-oxide-semiconductor) circuits to achieve higher sensitivity and smaller pixel size
23 than with other thermal sensors, such as thermoelectric (Oliver and Wise 1999) and SOI diode detectors (Tanaka et al.
24 1992). Thus, they are widely used for security, night vision, and autonomous driving (Kimata 2018) in MWIR and LWIR
25 applications.

26 Numerous materials have been studied for bolometers such as metals (gold (Au), platinum, titanium) and
27 semiconductors (vanadium oxide (Bonora et al. 2010), amorphous silicon (Bain et al. 2000)). In bolometers, the
28 temperature coefficient of resistance (TCR) is an important parameter. Metals typically have positive TCR and their
29 resistance increases with increasing temperature. In contrast, semiconductors have negative TCR and their resistance
30 decreases with increasing temperature. The TCR values of semiconductors are larger than those of metals, thus small
31 temperature changes can be detected.

32 Recently, advanced functional sensors with wavelength-selectivity for identification of substances through their
33 emission spectra in the MWIR and LWIR regions have been drawing significant attention. A spectroscopy is required to
34 realize wavelength-selectivity; however, this not only leads to high cost and large device size but also increases noise as
35 it emits infrared radiation to the sensor (Ogawa et al. 2018). To address this challenge, studies on various structures with
36 wavelength-dependent, such as plasmonic crystals (Ogawa et al. 2012) and metal insulator metal (MIM) (Hao et al. 2010)
37 have been performed (Ogawa et al. 2019). As described above, research on MWIR and LWIR detections has been
38 conducted; however, no research on thermal sensors for SWIR detection has been reported.

39 Therefore, a bolometer-type detector as an SWIR image sensor for low cost and miniaturization (by removing the
40 Peltier cooler and spectroscopy) has been proposed in this study, as shown in Figure 1. This device can be easily

1 fabricated using MEMS technology from an SOI wafer. In this device, SWIR radiation heats the absorber on the Si fixed
2 beam, which in turn changes its resistance with respect to its TCR value. This detector uses Au nanowire grating
3 structures coated with silicon as a wavelength-dependent SWIR absorber for multi-wavelength imaging without using a
4 spectroscope. Surface plasmon resonance (SPR) can be coupled with nanowire grating structures whose period is around
5 the wavelength of the incident light (Chen et al. 2016; Ongarello et al. 2011; Zilio et al. 2010). Localization of SPR also
6 occurs, which results in an electric field enhancement. This phenomenon leads to a strong absorption of incident light at
7 a specific wavelength band on a nanoscale metal structure. The absorption peak wavelength of the plasmonic structure
8 also depends on the surrounding refractive index. Thus, the Au nanowire grating structures are coated with Si, which has
9 high refractive index and excellent integration with MEMS fabrication processes. By adopting the above structures, an
10 absorber with a sharp absorption peak in the SWIR region can be fabricated. The optical characteristics of the plasmonic
11 structures can be controlled by their material, structure, and size (Li et al. 2014). In this study, we focused on the optical
12 characteristics when the lattice spacing of the Au nanowire grating structures was changed to easily fabricate the devices
13 with multiple absorption spectra on one SOI wafer. It was assumed that by arraying elements with different absorption
14 wavelength bands, spectral information of incident light can be obtained.

15 In this study, fabrication and evaluation of microbolometer devices integrated with a wavelength-dependent SWIR
16 absorber were carried out. The absorption spectra of the fabricated absorbers were measured, which have different grating
17 period of Au nanowires to control the wavelength of the absorption peaks. The electrical characteristics were also
18 measured at various device temperatures, light intensities, and wavelengths. The characteristics of an absorber-integrated
19 bolometer device that focuses on wavelength-dependent response according to the absorption spectrum with small
20 absorption change is reported in this paper.

21 **2. Measurement principle**

22 **2.1 Device structures**

23 For the bolometer proposed in this study, the light intensity P is measured based on the change in the electrical
24 resistance ΔR of the doubly clamped Si beam, which is caused by the temperature change ΔT when the absorber at the
25 center of the Si beam is irradiated with light. A schematic image of the device is shown in Fig. 1. To obtain high
26 sensitivity, the bolometer was designed in such a way that heat loss is suppressed. In particular, the heat conduction from
27 the Si beam to the substrate layer has a serious negative influence on the performance of the bolometer. Hence, the device
28 has a through hole to reduce heat loss from the beam. The elements that determine the electrical resistance and
29 temperature of the device are divided into three parts: the center pad with the Si absorber, the freestanding Si beam, and
30 the subsequent fixed Si beam on the buried-oxide (BOX) layer, as shown in Fig. 1. The electrical resistance is determined
31 by their sum. The center pad with an optical absorber is supported by narrow Si beams fixed at both ends, indicating the
32 freestanding structure. The freestanding length of the Si beam from the edge of the center pad to the edge of the through
33 hole was 500 μm . The width and thickness of the freestanding Si beam were 10 and 1.5 μm , respectively. The electrical
34 resistance of the Si beam was measured via electrode pads fabricated on both sides.

35 **2.2 Theory**

36 The important figure of merit for the resistance bolometer is a temperature coefficient of resistance (TCR) α defined as
37 follows:

$$\alpha = \frac{1}{R_0} \frac{\Delta R}{\Delta T} \quad (1)$$

1 where R_0 is the initial electrical resistance. While a Si beam with a uniform cross-section and a length of $2l$ is
 2 considered as a simple model, the temperature distribution in the longitudinal direction of the beam $dT(x)/dx$ can be
 3 derived by solving the one-dimensional Fourier law as follows:

$$\frac{dT(x)}{dx} = -\frac{\beta P}{2bh\kappa} \quad (2)$$

4 where κ , P , and β denote the thermal conductivity, irradiating light intensity to the absorber, and wavelength-
 5 dependent light absorption rate, respectively. The width and thickness of the Si beam are represented by b and h ,
 6 respectively. The average temperature change of the Si beam ΔT can be obtained by integrating the length of the Si
 7 beam $2l$ as follows:

$$\Delta T = \frac{1}{2l} \int_{-l}^l \left\{ -\frac{\beta P}{2bh\kappa} (|x - l|) \right\} dx = \frac{l}{4bh\kappa} \beta P \quad (3)$$

8 Thus, the resistance change ΔR can be expressed as a function of the temperature change of Si beam ΔT and the light
 9 intensity P as follows:

$$\Delta R = \alpha \Delta T R_0 = \frac{\alpha l R_0}{4bh\kappa} \beta P \quad (4)$$

10 **3. Analytical and experimental methods**

11 **3.1 Analytical method**

12 To investigate the influence of light intensity on the temperature of the device, thermal analysis was performed using the
 13 finite element method (FEM). The design dimensions shown in Fig. 1 were used for the analytical model. The
 14 temperature at the bottom of the substrate was fixed at the initial temperature of 27°C. A heating area of $20 \mu\text{m} \times 20 \mu\text{m}$,
 15 which is equal to the dimension of the absorber, was set at the center. The absorption rate was assumed to be 43.2%
 16 based on the measurement results of the absorption of the Au nanowire grating structures shown in Sec. 4.3. A heat
 17 quantity ranging from 0.000 to 0.432 mW was applied to the heating area for the analysis, corresponding to a light
 18 intensity ranging from 0.0 to 1.0 mW considering an absorption of 43.2%. A theoretical calculation was also performed
 19 using Eq. (3) to obtain the average temperature of the Si beam.

20 **3.2 Device fabrication**

21 An SOI wafer with a device layer thickness of 1.5 μm , a BOX layer thickness of 0.25 μm , and a Si substrate thickness
 22 of 540 μm was used for device fabrication. First, chromium (Cr) masks for the through hole, which were made through
 23 Deep-RIE (reactive ion etching), were fabricated on the back surface of the substrate using Cr vacuum deposition,
 24 photolithography, and Cr etching. Aluminum (Al) patterns of electrodes with dimensions $250 \mu\text{m} \times 250 \mu\text{m}$ and absorbers
 25 with dimensions $30 \mu\text{m} \times 30 \mu\text{m}$ were fabricated on the front surface of the device layer using Al vacuum deposition,
 26 photolithography, and Al etching. Then, they were annealed to obtain an ohmic junction at the interface between Si and
 27 Al. Subsequently, the Al patterns were overlaid with the Au patterns of electrodes and absorbers using photolithography,
 28 Au vacuum deposition, and lift-off processes. The Au nanowires were arranged on the Au thin film with lines and spaces
 29 and fabricated using electron-beam (EB) lithography, Au deposition, and lift-off processes. The Au nanowires, each with
 30 a width of 100 nm, a height of 50 nm, and a grating period of 400–800 nm, were fabricated. Then Au nanowires were
 31 coated with Si by sputtering to obtain an absorption peak in the near-infrared wavelength. The coating Si thickness was
 32 100 nm. After the through hole was fabricated using Deep-RIE, the sputtered Si and the beam were patterned using

1 photolithography and subsequent Si dry etching. Finally, the BOX layer was removed from the backside using buffered
2 hydrofluoric acid.

3 **3.3 Optical characterization**

4 The absorption rate β [%] of the absorber is expressed as $\beta = 100 - T - R$, where T [%] and R [%] denote the
5 transmittance and reflectance, respectively. It was assumed that $T = 0$ without considering transmission as the Au layer
6 thickness of 100 nm was too thick to be penetrated. The reflectance was measured using a microscopic spectrometer
7 (MSV-5200, JASCO) and calibrated using the reflectance of the Au film. The measurement wavelength ranged from
8 1000 to 1800 nm.

9 **3.4 Bolometer characterization**

10 The electrical characteristics of the fabricated devices were measured. First, the device electrodes were connected to the
11 printed circuit board by Au wire bonding. The electrical current was measured while a DC voltage was applied between
12 the electrodes using a DC power supply. The applied voltage was determined to be 0.3 V, which produced small noise
13 and Joule heat effects based on the preliminary experiments. A Peltier device was set under the bolometer chip to control
14 the device temperature by 1°C from 27 to 40°C. The near-infrared was irradiated onto the absorber placed on the Si beam
15 by selecting the intensity and wavelength using a wavelength-tunable laser. The output wavelength of the laser used in
16 this study ranged from 1530 to 1565 nm. The intensity was adjusted between 0.240 and 0.485 mW. To reduce electrical
17 noise and external light, the device was placed in an Al case.

18 **4. Results and discussions**

19 **4.1 Analytical**

20 Figures 2(a) – (b) show the FEM analytical results of the device temperature distribution when a heat quantity of 0.432
21 mW was applied. Figure 2(b) shows the temperature distribution in the longitudinal direction. The temperature in the
22 center-pad region was almost constant because of its high thermal conductivity owing to its large cross-sectional area.
23 The temperature of the freestanding-beam region decreased along the longitudinal direction according to the Fourier law
24 shown in Eq. (2). For the fixed-beam region, it was confirmed that the temperature at the fixed end of the beam did not
25 change due to heat conduction to the substrate. The average temperature changes in the center pad, freestanding beam,
26 and fixed-beam regions were 46.3, 23.1, and 0.025°C, respectively. The temperature change in the fixed-beam region
27 could be considered negligible as it was significantly smaller than that of the freestanding-beam region. The resistance
28 of the fixed Si beam was thought not to change.

29 Figure 2(c) shows the average temperature in the freestanding-beam region calculated using the FEM analysis and Eq.
30 (3). From the analytical result, it was found that the temperature of the freestanding Si beam increased linearly in
31 proportion to the light intensity as the amount of heat transferred to the Si beam increased with light intensity. Therefore,
32 this confirms the validity of the theoretical calculation as its result agreed well with that of the FEM analysis.

33 **4.2 Device fabrication**

34 Figure 3 shows the scanning electron microscopy (SEM) image of the fabricated device. As we designed, a freestanding
35 Si beam was successfully fabricated from an SOI wafer as shown in Fig. 3(a), integrating the Au nanowire grating
36 structure at the center of the beam as an optical absorber as shown in Figs. 3(b) and (c). The measured lengths of the

1 freestanding Si beam and the fixed Si beam on the BOX layer were 500 and 50 μm , respectively. The measured width
2 of the beams was 10 μm .

3 **4.3 Optical characterization**

4 Figure 4 shows the measured optical absorption spectra after fabrication of the Au nanowire grating structures. It was
5 confirmed that the absorber with Si-deposited grating gold nanowires had absorption peaks in the SWIR wavelength
6 range. This was based on the result of the absorber, which shows that only the sputtered Si without Au nanowire structure
7 and Au nanowire grating structure without sputtered Si had no large peaks. The sputtered Si produced a broad peak at
8 around 1700 nm because of the interference at the interfaces of the sputtered Si thin film. The absorber with a grating
9 period of $p = 400$ nm had its first absorption peak at 1292 nm and second peak at 1472 nm. The absorber with a grating
10 period of $p = 500$ nm had its first peak at 1366 nm and second peak at 1675 nm. In addition, the absorber with a grating
11 period of $p = 600$ nm had its first peak at 1377 nm and second peak at 1771 nm. These results confirm that both the
12 first and second absorption peaks shifted to longer wavelengths as the grating period increased. The absorbers with
13 grating periods of 700 and 800 nm had single peak as the second peak was assumed to appear at wavelengths longer than
14 1800 nm. An absorber with a single peak in the SWIR wavelength is desirable for obtaining an intensity measurement
15 at each wavelength band without using a spectroscope. In the future, it will be necessary to optimize the structures and
16 dimensions of the absorbers for obtaining the desired absorption characteristics.

17 **4.4 Bolometer characterization**

18 Figure 5 shows the current-voltage (IV) measurement results of the fabricated devices. Ohmic junction characteristics
19 can be obtained by annealing the interface between Al and Si at the electrode pads.

20 Figures 6(a) and (b) show the measured resistance for a grating period of $p=400$ nm as a function of the device
21 temperature controlled by the Peltier device and the light intensity, respectively. The wavelength used in this
22 measurement was 1530 nm. It was found that resistance decreased linearly with device temperature and light intensity.
23 This result shows similar pattern as that of the theoretical calculation in Eq. (4) as the TCR values of semiconductors,
24 such as Si, are negative and can be considered constant in small temperature changes. From Fig. 6(a), the measured
25 resistances at 27 and 40°C were 51.9 and 43.8 M Ω , respectively, characterized by a linear relationship and which resulted
26 in a TCR value of -0.012 /°C as calculated using Eq. (1). In this case, the temperature of the Si beam was considered
27 constant as the device chip was heated from the backside using the Peltier device. The resistance of 52.3 M Ω without
28 light irradiation decreased linearly to 48.6 M Ω at a light intensity of 0.485 mW.

29 The temperature change as a function of light intensity was calculated based on Figs. 6(a) and (b). The resistance
30 change of the device under light irradiation was determined from the sum of the resistance changes of the three parts:
31 the center pad, the freestanding-beam, and the fixed-beam regions. Both resistance changes of the center pad and the
32 fixed-beam regions were negligible as the resistance and temperature changes were significantly smaller than those of
33 the freestanding-beam region. The resistance of the center-pad region and the temperature change of the fixed-beam
34 region were hundred-times and 940-times smaller than those of the freestanding-beam region, respectively. Thus, the
35 resistance change was determined only from the freestanding-beam region using the following equation:

$$\Delta R = \alpha \Delta T_b R_{b0} \quad (5)$$

36 Here, ΔT_b and R_{b0} are the temperature change and initial resistance of the freestanding-beam region, respectively.
37 ΔT_b can be calculated using Eq. (5) and the experimental α and ΔR . Figure 6(c) shows the relationship between the
38 light intensity and the temperature of the freestanding Si beam calculated using Eq. (5) and based on the measurement
39 results shown in Figs. 6(a) and (b). It was found that the temperature of the freestanding Si beam increased linearly with

light intensity by the photothermal conversion of the absorber. The calculated temperature of freestanding Si beam under 0.485 mW laser irradiation was 6.5°C. The reason for this smaller temperature change compared to the 23.1°C from the FEM analysis shown in Fig. 2(d) could be the large heat dissipation effect due to transfer to the atmosphere, which was not considered in the analysis. Therefore, measurements in vacuum are required in the future to improve the sensitivity.

This paragraph discusses the dependency of resistance change on laser wavelength. Assuming the temperature change of freestanding Si beam due to absorption of light is small, the temperature coefficient of resistance α can be regarded constant. Thus, sensitivity $\Delta R/P$ is proportional to freestanding Si beam temperature change ΔT_b and light absorption rate β , which depends on wavelength. In this study, we focused on the dependence of light absorption rate β on sensitivity. To compare sensitivity with absorption rate β as a function of wavelength λ , the normalized sensitivity and the normalized absorption rate were calculated using the following equations:

$$S(\lambda) = \left(\frac{\Delta R_\lambda}{P_\lambda} \right) / \left(\frac{\Delta R_{1530\text{nm}}}{P_{1530\text{nm}}} \right) \quad (6)$$

$$A(\lambda) = \beta_\lambda / \beta_{1530\text{nm}} \quad (7)$$

where $S(\lambda)$ and $A(\lambda)$ denote the normalized sensitivity and normalized absorption rate based on the wavelength of $\lambda = 1530$ nm, respectively.

Figures 7(a) and (b) show the sensitivity and absorption rate of the two devices at $p=400$ nm and 800 nm and at wavelengths ranging from 1530 to 1565 nm. Figures 7(c) and (d) show the relationship between normalized sensitivity and normalized absorption rate. The absorption rate at $p=400$ nm tended to increase from 43.2% to 44.7% as the wavelength increased from 1530 to 1565 nm as shown in Fig. 7(a), corresponding to the normalized absorption rate $A(\lambda)$ from 1.0 to 1.03 in Fig. 7(c). In contrast, the absorption at $p=800$ nm tended to decrease from 60.1% to 52.8% as the wavelength increased from 1530 to 1565 nm as shown in Fig. 7(b), corresponding to the normalized absorption $A(\lambda)$ from 1.0 to 0.88 in Fig. 7(d). We chose these devices to investigate the dependency of wavelength-dependent absorption on relative sensitivity. The resistance changes at $p = 400$ and 800 nm are shown in Figs. 7(a) and (b), respectively, also exhibit increasing and decreasing relationships with wavelength, respectively. Although the two devices showed both increasing and decreasing absorption trends, the trends for the normalized sensitivity $S(\lambda)$ and normalized absorption $A(\lambda)$ are in good agreement as well as those values. Depending on the wavelength, the small $S(\lambda)$ change of 1% or less matched well with $A(\lambda)$

It was confirmed that the absorber-integrated bolometer device enabled wavelength-dependent response according to the absorption spectrum and detection of small absorption change (1% or less) as the resistance changed. The developed devices could provide low-cost and miniaturized SWIR spectrometers.

5. Conclusion

This study proposed a bolometer-type detector element with wavelength-dependent fabricated from an SOI wafer as an SWIR image sensor element for low cost and miniaturization. Although bolometers have lower detection sensitivity compared to conventional photon detectors, they can be operated at room temperature and do not require Peltier coolers. In addition, it was expected that wavelength-selectivity imaging could be realized without a spectroscope by adopting Au nanowire grating structures that strongly absorb a specific wavelength of SWIR caused by surface plasmon resonance as the optical absorber. Devices with Au nanowire grating structures on a doubly clamped Si beam were fabricated using MEMS technology. It was confirmed that the fabricated Au nanowire grating structures had absorption peaks in the SWIR and the absorption peaks shifted to longer wavelengths as the grating period increased. To evaluate the proposed

1 devices, electrical characteristics at device temperatures ranging from 27 to 40°C at 1°C increment and SWIR light
2 intensity ranging from 0.240 to 0.485 mW were measured. It was found that electric resistance decreased linearly with
3 increasing temperature and light intensity and showed similar trends in both the theoretical calculation and FEM analysis.
4 In the future, measurement in vacuum is required to suppress heat loss and improve sensitivity as the experimental
5 temperature change was much smaller than the analytical result. The resistance at wavelengths ranging from 1530 to
6 1565 nm at 5 nm increments were evaluated. It was confirmed that the absorber-integrated bolometer device enabled
7 wavelength-dependent response according to the absorption spectrum and detection of small absorption change (1% or
8 less) as the resistance changed. It was shown that the device could serve as an SWIR imaging element without requiring
9 a spectroscope and a cooler, thereby reducing cost and size.

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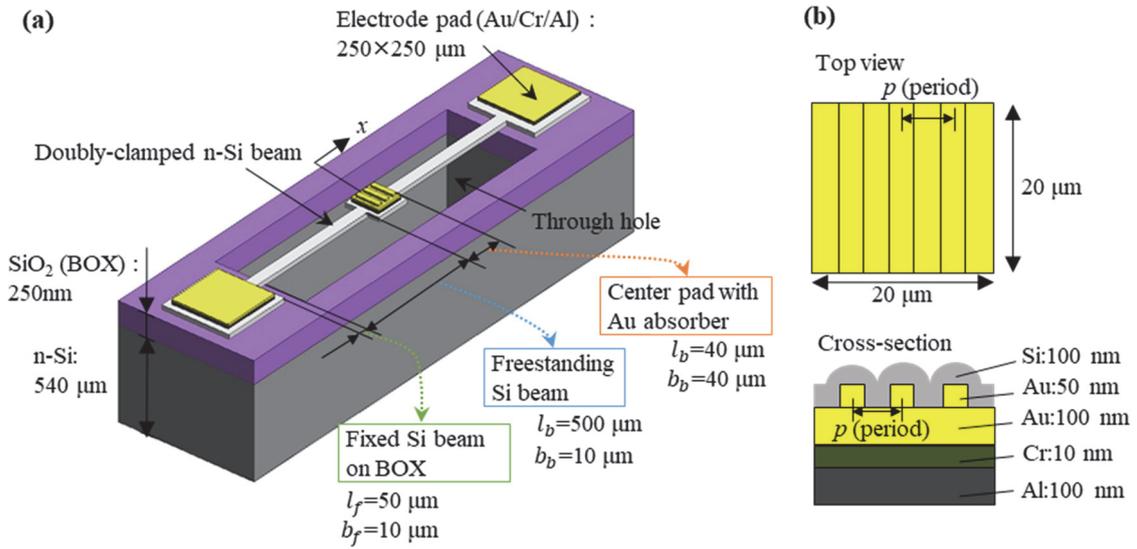
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1 **Figures**

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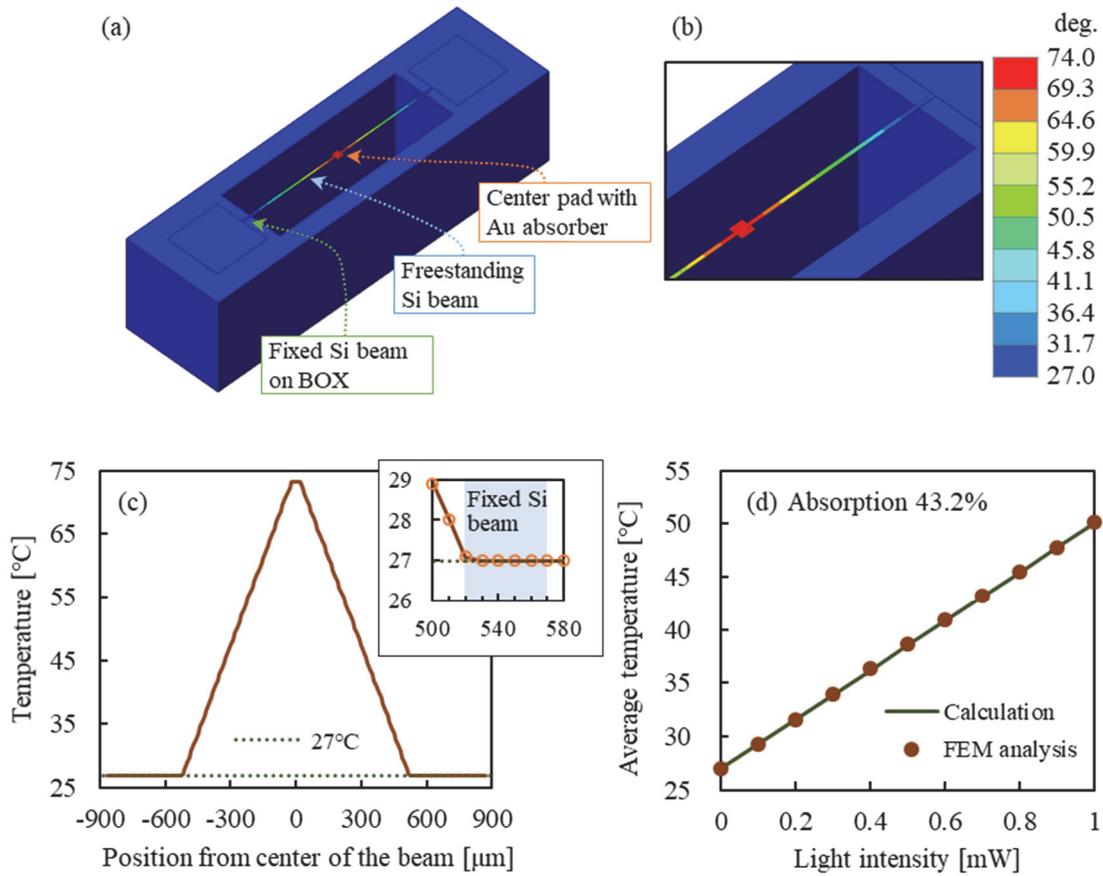
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5 **Fig. 1** Bolometer-type SWIR detector device with an SWIR absorber fabricated using an SOI wafer. (a) Schematic
 6 image of the detector. The freestanding Si beam was fixed at both ends. The absorber was located at the center pad of
 7 the beam ($40 \mu\text{m} \times 40 \mu\text{m}$). The narrow Si beam for supporting the center pad was divided into freestanding Si beam and
 8 fixed Si beam on the BOX layer, with lengths of $500 \mu\text{m}$ and $50 \mu\text{m}$, respectively. (b) Schematic of the absorber with
 9 gold nanowire grating structure covered with the sputtered Si thin film. The period was varied from 400 to 800 nm .

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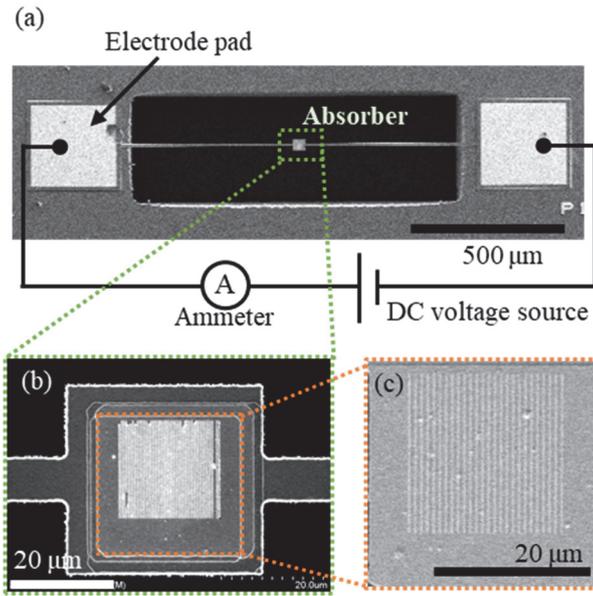


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3 **Fig. 2** Analytical results (a), (b) Contour plot of the temperature of the fabricated device with 1 mW heat injection to
 4 the Au absorber calculated through FEM simulation. Plot (b) shows the magnified image of (a). (c) Relationship between
 5 beam position from the center of the beam and temperature at a light intensity of 1 mW calculated through FEM
 6 simulation. (d) The average temperature of the Si beam with light intensity changing from 0 to 1 mW calculated through
 7 FEM analysis and Eq. 3. The absorption was set at 43.2% in all calculations.

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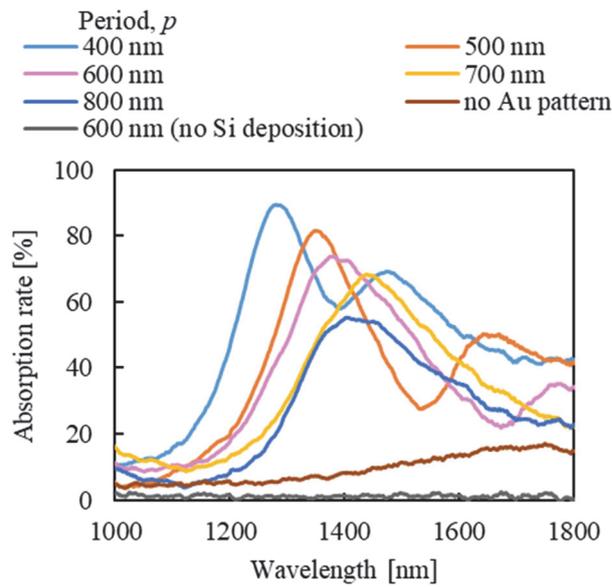
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3 **Fig. 3** SEM images of the fabricated devices. (a) Freestanding Si beam fabricated from an SOI wafer. The Si beam is
4 connected to the ammeter and DC voltage source for electrical characterization. (b) Absorber at the center of the beam
5 (c) Absorber with the gold nanowire grating structures.

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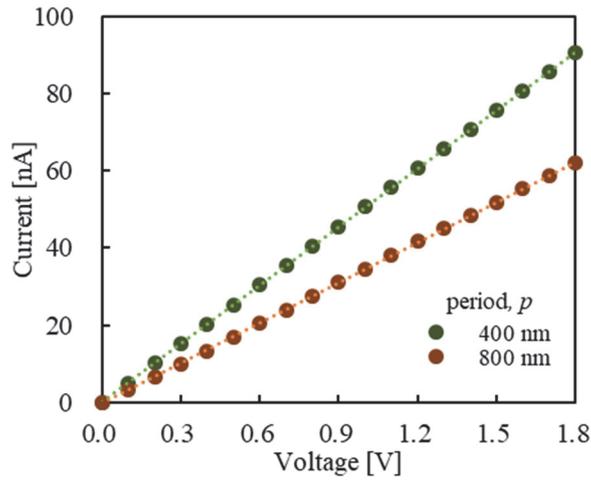


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10 **Fig. 4** The measured optical absorption spectra of the gold nanowire grating structures with period (p) ranging from
11 400 to 800 nm. Absorption spectra for sputtered Si without gold nanowire structures and non-sputtered absorber with
12 period $p = 600$ nm are also shown.

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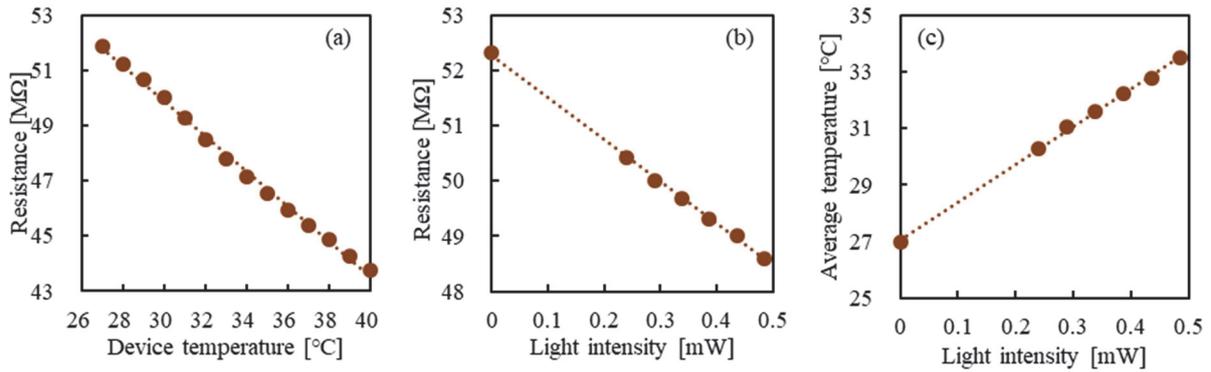
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3 **Fig. 5** The measured current with applied DC voltage ranging from 0 to 1.8 V. Periods of 400 nm and 800 nm were
4 used for the Au nanowire grating structures.

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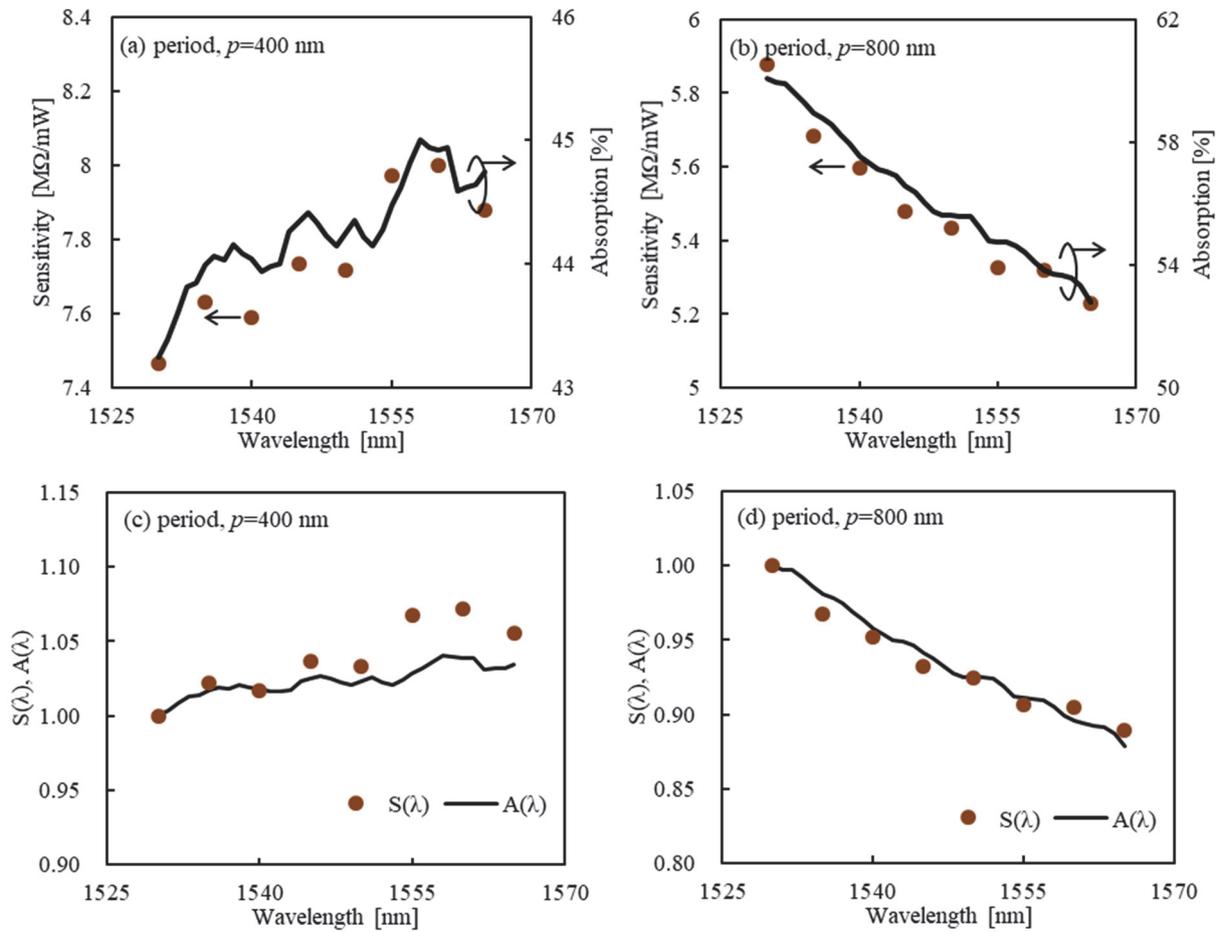


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9 **Fig. 6** Electrical measurements for the device at a period of 400 nm. (a) Relationship between device temperature and
10 resistance with device temperature ranging from 27°C to 40°C. (b) Relationship between near-infrared irradiation light
11 intensity and resistance with light intensity ranging from 0 to 0.485 mW, when the laser wavelength was 1530 nm. (c)
12 Relationship between light intensity and device temperature calculated using the results (a) and (b), and Eq. 4.

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4 **Fig. 7** Wavelength-dependent responses. (a) Measured sensitivity and absorption with the grating period of 400 nm,
5 (b) Measured sensitivity and absorption with the grating period of 800 nm, (c) normalized sensitivity $S(\lambda)$ and normalized
6 absorption $A(\lambda)$ with the grating period of 400 nm, (d) normalized sensitivity $S(\lambda)$ and normalized absorption $A(\lambda)$ with
7 the grating period of 800 nm. The wavelength ranges from 1530 to 1565 nm.

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